Silicon NPN Power Transistors 2SD555

DESCRIPTION

·With TO-3 package
·High power dissipation
·Complement to type 2SB600

APPLICATIONS

·For high speed ,high current ,high power applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	250	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		10	A
P_C	Collector power dissipation	T_C=25□	200	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance junction to case	1.46	□/W

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA ;I_B=0	200			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	5			V
$V_{CEsat-1}$	Collector-emitter saturation voltage	I_C=5A; I_B=0.5A			1.5	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	I_C=10A; I_B=2A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=5A; I_B=0.5A			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=250V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=2A ; V_{CE}=5V	40		200	
C_{OB}	Collector output capacitance	I_E=0 ; V_{CB}=10V;f=1MHz		300		pF
f_T	Transition frequency	I_C=1A ; V_{CE}=10V		15		MHz

PACKAGE OUTLINE

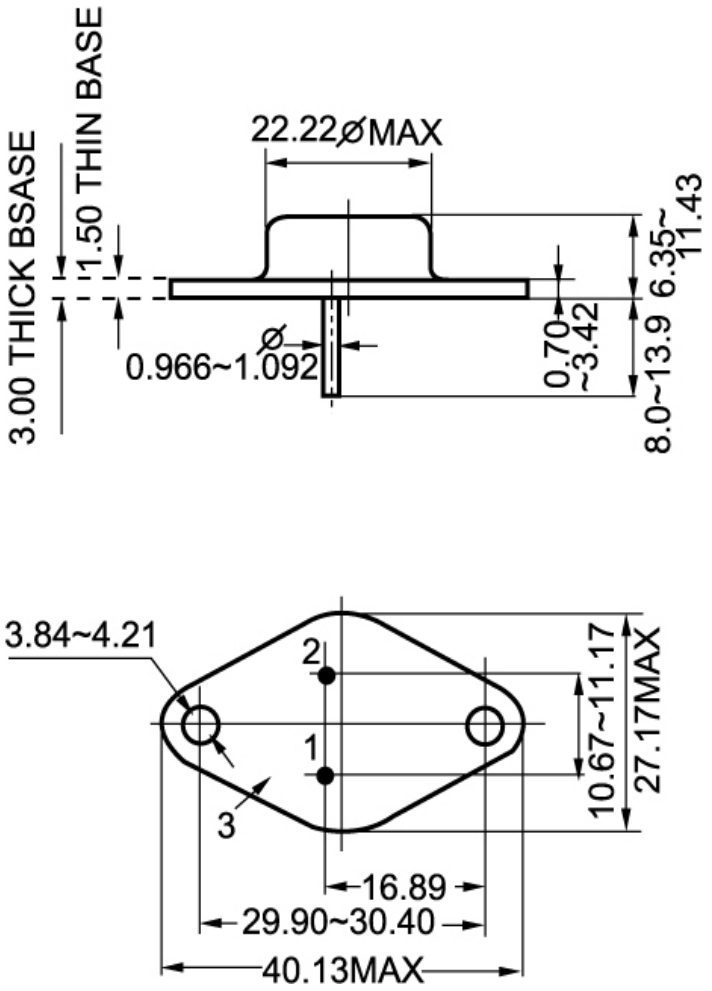

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)